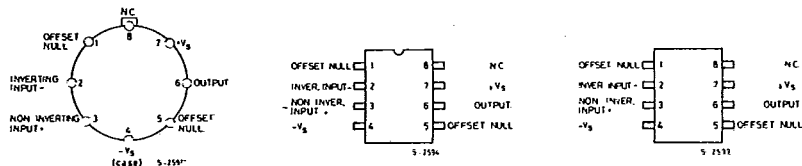


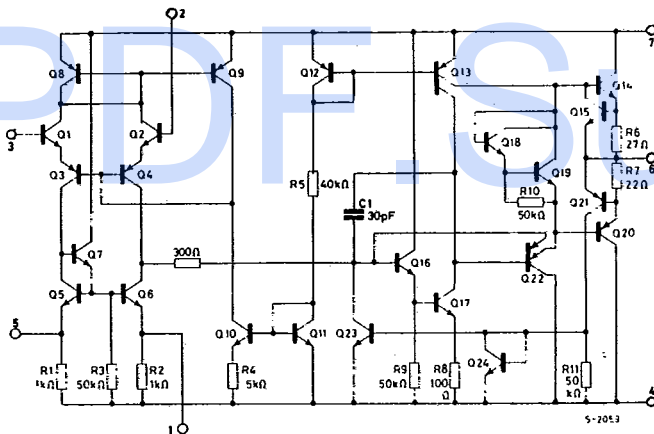
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CONNECTION DIAGRAMS AND ORDERING NUMBERS



Type	TO-99	Minidip	SO-8
LS 141	LS 141 TB	—	—
LS 141A	LS 141 ATB	—	—
LS 141C	LS 141 CTB	LS 141 CB	LS 141 CM
LS 8141	—	—	LS 8141M
LS 8141A	—	—	LS 8141 AM
LS 8141C	—	—	LS 8141 CM

SCHEMATIC DIAGRAM



THERMAL DATA

	TO-99	Minidip	SO-8
$R_{th j-amb}$ Thermal resistance junction ambient	max 155 °C/W	120 °C/W	200* °C/W

* Measured with the device mounted on a ceramic substrate (25 x 16 x 0.6 mm)

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ELECTRICAL CHARACTERISTICS (see note)

Parameter	Test conditions	LS 141			LS 141A			LS 141C			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
V_{os} Input offset voltage	$T_{amb} = 25^{\circ}\text{C}$ $R_g < 10\text{ k}\Omega$ $R_g < 50\ \Omega$		1	5		0.8	3		2	6	mV mV
	$T_{amb} = T_{min}$ to T_{max} $R_g < 10\text{ k}\Omega$ $R_g < 50\ \Omega$			6			4			7.5	mV mV
ΔV_{os} Input offset voltage adjust. range	$V_s = \pm 20\text{V}$				± 10						mV
	$V_s = \pm 15\text{V}$ $T_{amb} = 25^{\circ}\text{C}$		± 15						± 15		mV
$\frac{\Delta V_{os}}{\Delta T}$ Average input offset voltage drift						15					$\frac{\mu\text{V}}{^{\circ}\text{C}}$
I_{os} Input offset current	$T_{amb} = 25^{\circ}\text{C}$		20	200		3	30		20	200	nA nA
	$T_{amb} = T_{min}$ to T_{max}		85	500			70			300	nA
$\frac{\Delta I_{os}}{\Delta T}$ Average input offset current drift						0.5					$\frac{\text{nA}}{^{\circ}\text{C}}$
I_b Input bias current	$T_{amb} = 25^{\circ}\text{C}$		80	500		30	80		80	500	nA μA
	$T_{amb} = T_{min}$ to T_{max}			1.5			0.21			0.8	μA
R_i Input resistance	$T_{amb} = 25^{\circ}\text{C}$	0.3	2		1	6		0.3	2		M Ω M Ω
	$T_{amb} = T_{min}$ to T_{max}				0.5						M Ω
V_i Input voltage range	$T_{amb} = T_{min}$ to T_{max}	± 12	± 13		± 12	± 13		± 12	± 13		V
G_v Large signal voltage gain	$T_{amb} = 25^{\circ}\text{C}$ $R_L \geq 2\text{ k}\Omega$ $V_s = \pm 15\text{V}$ $V_o = \pm 10\text{V}$	94	106		94			86	106		dB
	$T_{amb} = T_{min}$ to T_{max} $R_L \geq 2\text{ k}\Omega$ $V_s = \pm 15\text{V}$ $V_o = \pm 10\text{V}$ $V_s = \pm 5\text{V}$ $V_o = \pm 2\text{V}$	88			90 80			84			dB
V_o Output voltage swing	$V_s = \pm 15\text{V}$ $R_L \geq 10\text{ k}\Omega$ $R_L \geq 2\text{ k}\Omega$	± 12 ± 10	± 14 ± 13		± 12 ± 10	± 14 ± 13		± 12 ± 10	± 14 ± 13		V V
	$T_{amb} = 25^{\circ}\text{C}$ $T_{amb} = T_{min}$ to T_{max}		25		10 10	25 40	35	25			mA mA
CMR Common mode rejection	$V_s = \pm 20\text{V}$ $R_g \leq 10\text{ k}\Omega$ $V_{CM} = \pm 12\text{V}$	70	90		80	95		70	90		dB
SVR Supply voltage rejection	$R_g \leq 50\ \Omega$ $V_s = \pm 5$ to $\pm 20\text{V}$ $R_g \leq 10\text{ k}\Omega$ $V_s = \pm 5$ to $\pm 15\text{V}$	77	96		86	96		77	96		dB dB



ELECTRICAL CHARACTERISTICS (continued)

Parameter	Test conditions	LS 141			LS 141A			LS 141C			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
Transient respon. (unity gain) Rise time Overshoot	$T_{amb} = 25^{\circ}C$		0.3 5			0.25 6	0.8 20		0.3 5		μs %
B Bandwidth	$T_{amb} = 25^{\circ}C$				0.437	1.5					MHz
SR Slew rate	$T_{amb} = 25^{\circ}C$		0.5		0.3	0.7			0.5		V/ μs
I_s Supply current	$T_{amb} = 25^{\circ}C$		1.7	2.8					1.7	2.8	mA
P_{tot} Power consumption	$T_{amb} = 25^{\circ}C$ $V_s = \pm 20V$ $V_s = \pm 15V$		50	85		80	150		50	85	mW mW
	$V_s = \pm 20V$ $T_{amb} = T_{min}$ $T_{amb} = T_{max}$						165 135				mW mW
	$V_s = \pm 15V$ $T_{amb} = T_{min}$ $T_{amb} = T_{max}$		60 45	100 75							mW mW

Note: These specifications, unless otherwise specified, apply for $V_s = \pm 15V$ and $T_{amb} = -55$ to $125^{\circ}C$ for LS 141 and LS 141A. For the LS 141C these specifications apply for $T_{amb} = 0$ to $70^{\circ}C$

Fig. 1 - Open loop voltage gain vs. supply voltage

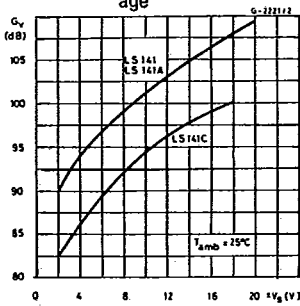


Fig. 2 - Output voltage swing vs. supply voltage

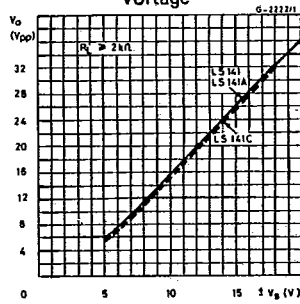
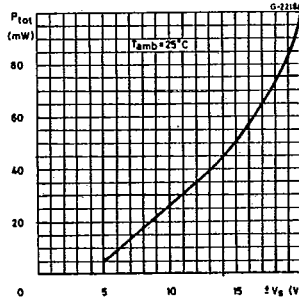
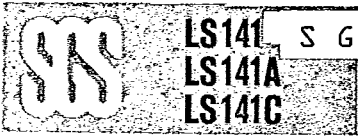


Fig. 3 - Power consumption vs. supply voltage





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Fig. 4 - Open loop voltage gain vs. frequency

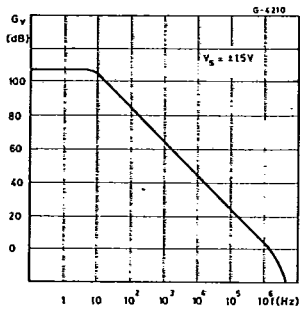


Fig. 5 - Open loop phase response vs. frequency

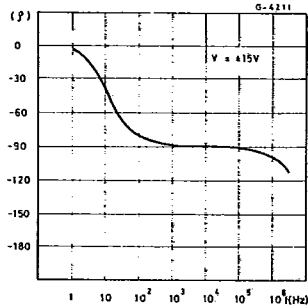


Fig. 6 - Input offset current vs. supply voltage (for LS 141 and LS 141C)

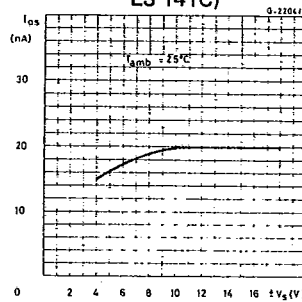


Fig. 7 - Input resistance and capacitance vs. frequency (for LS 141 and LS 141C)

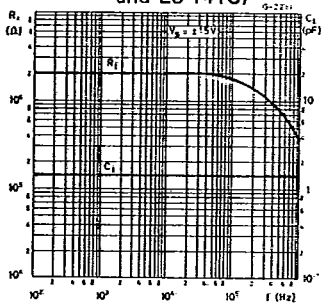


Fig. 8 - Output resistance vs. frequency

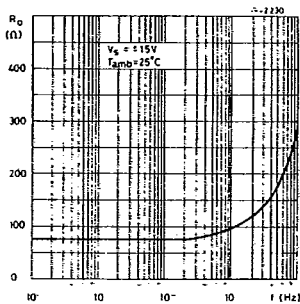


Fig. 9 - Output voltage swing vs. load resistance

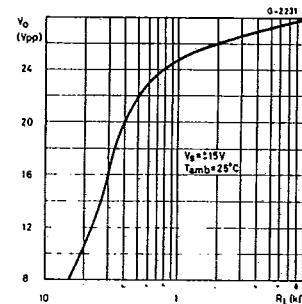


Fig. 10 - Output voltage swing vs. frequency

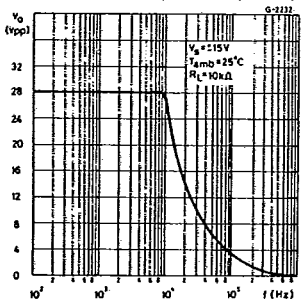


Fig. 11 - Input noise voltage vs. frequency

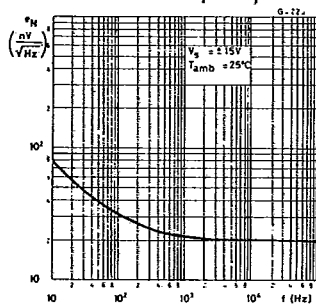
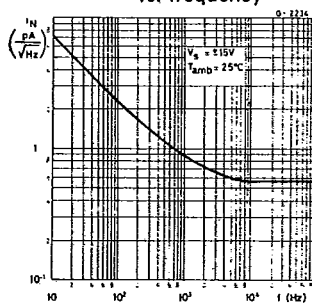
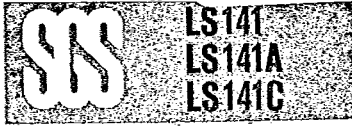


Fig. 12 - Input noise current vs. frequency





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Fig. 13 - Transient response

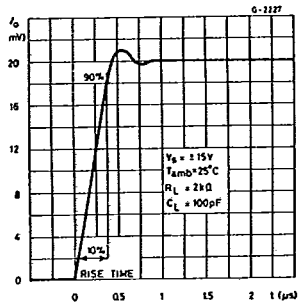


Fig. 14 - Common mode rejection ratio vs. frequency

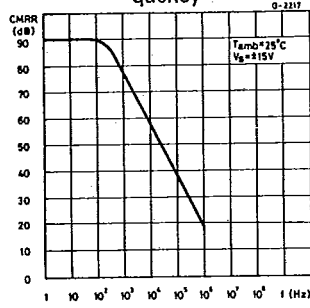
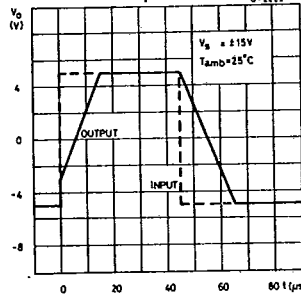


Fig. 15 - Voltage follower large signal pulse response



Typical performance curves for LS 141 and LS 141A

Fig. 16 - Input bias current vs. ambient temperature

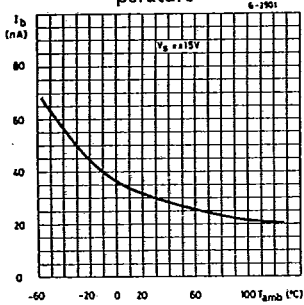


Fig. 17 - Input resistance vs. ambient temperature

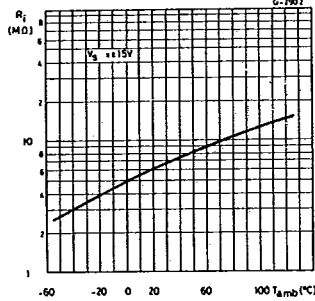


Fig. 18 - Input offset current vs. ambient temperature

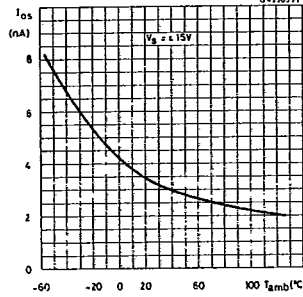


Fig. 19 - Output short-circuit current vs. ambient temperature

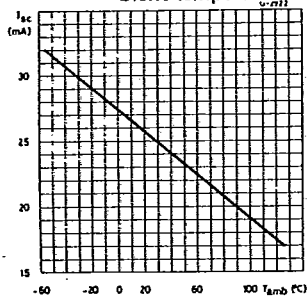


Fig. 20 - Power consumption vs. ambient temperature

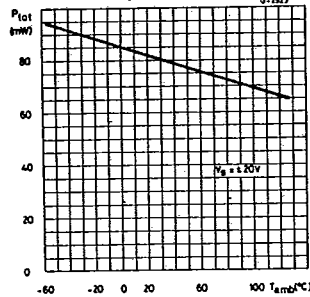
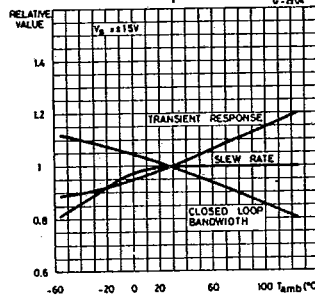


Fig. 21 - Frequency characteristics vs. ambient temperature





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Typical performance curves for LS 141C

Fig. 22 - Input bias current vs. ambient temperature

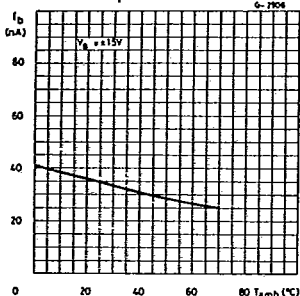


Fig. 23 - Input resistance vs. ambient temperature

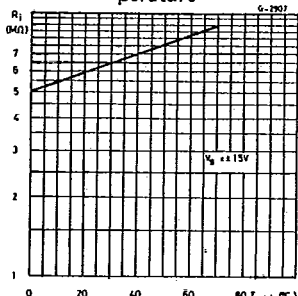


Fig. 24 - Input offset current vs. ambient temperature

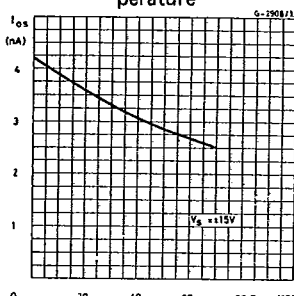


Fig. 25 - Output short circuit current vs. ambient temperature

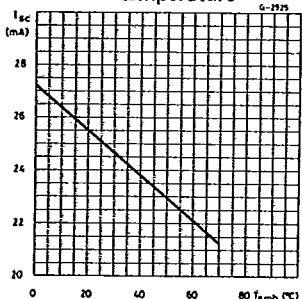


Fig. 26 - Power consumption vs. ambient temperature

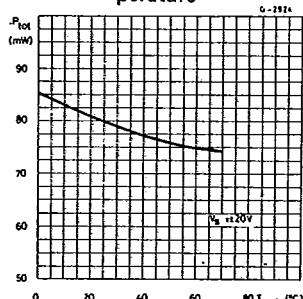
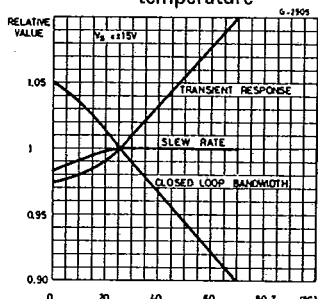


Fig. 27 - Frequency characteristics vs. ambient temperature



TYPICAL APPLICATIONS

Fig. 28 - Clipping amplifier

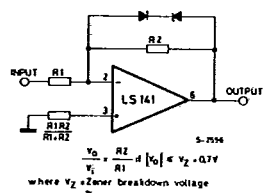


Fig. 29 - Simple integrator

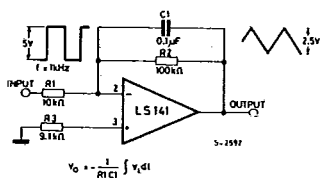


Fig. 30 - Simple differentiator

